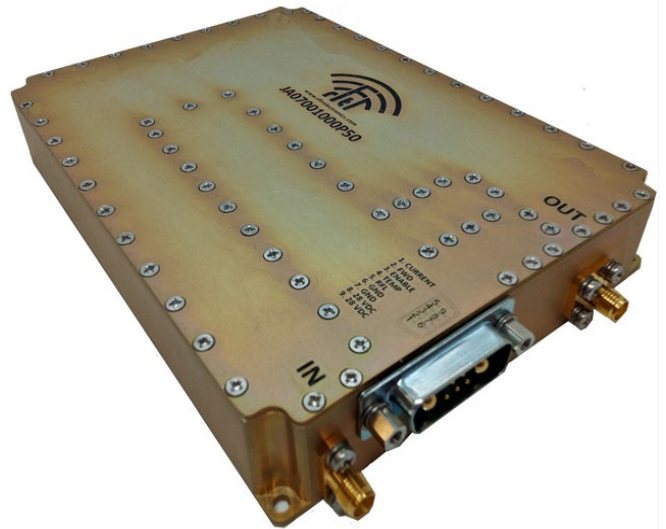




JA07001000P50; 0.7 – 1 GHz 100W AMPLIFIER

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Forward/Reflected Power Monitorings
- Fast Switching Capability



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

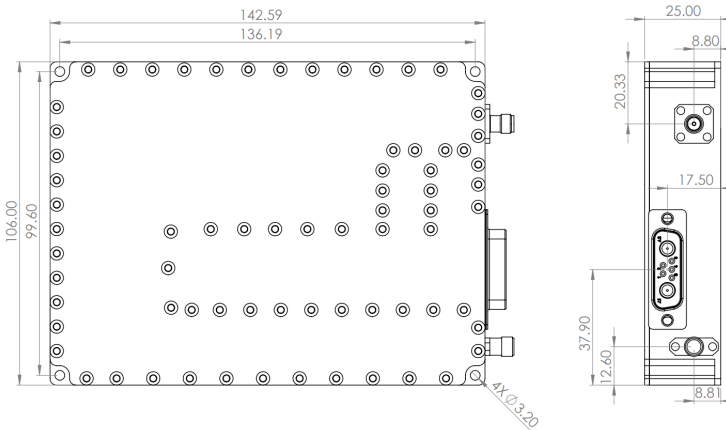
Frequency:	700 - 1000 MHz
Output Power:	100 W typ.
RF input for Rated Output:	0 dBm typ.
Nominal Gain:	50 dB typ.
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 (Fully Protected)
DC Supply Voltage:	28 V
DC Current:	8.5 A Avg typ.
Enable Speed:	5 μs max.
Operating Case Temp.:	-40 °C to 85 °C External Heatsink Required
Storage Temperature:	-40 °C to 85 °C

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
7-PIN DSUB:	A1) GND A2) 28V 1) Current 2) Forward Power 3) Enable 4) Temperature 5) Reverse Power

MECHANICAL SPECIFICATIONS

Size (mm) :	142.6 x 106 x 25
Weight :	600 gr.
Plating :	Yellow Chromate



GENERAL DESCRIPTION

RFTR's JA07001000P50 is a reliable ultrawide-band 100W power amplifier operating between 700-1000 MHz and suitable for CW or Pulsed waveforms. This amplifier can be used in different applications such as radars, datalinks, mobile jamming or UAVs. JA07001000P50 offers forward-reverse power monitoring and survives under ∞:1 load VSWR condition. The PA can be enabled/disabled as fast as 5 μs that makes it suitable for power saving during pulsed applications.

JA07001000P50 is designed with the components that do not require any export license.